

2SD1441

Silicon NPN Triple-Diffused Junction Mesa Type

Horizontal Deflection Output

■ Features

- Damper diode built-in
- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)

■ Absolute Maximum Ratings (T_c=25°C)

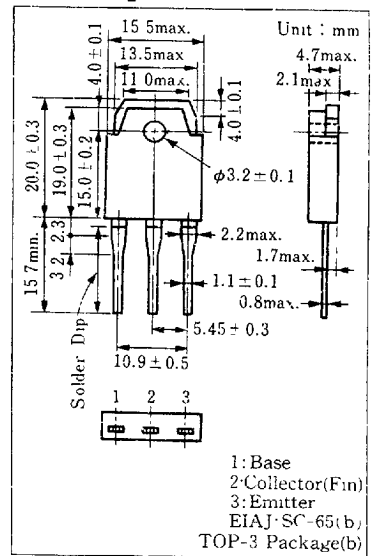
Item	Symbol	Value	Unit
Collector-base voltage	V _{CB0}	1500	V
Collector-emitter voltage	V _{CE0}	1500	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	4	A
Peak collector current	I _{CP} *	15	A
Peak base current	I _{BP}	3.5	A
Reverse peak base current	I _{BRP}	-2.5	A
Collector power dissipation	P _C	T _c =25°C	70
		T _a =25°C	2.5
Junction temperature	T _j	130	°C
Storage temperature	T _{stg}	-55 ~ +130	°C

* Non repetitive peak value

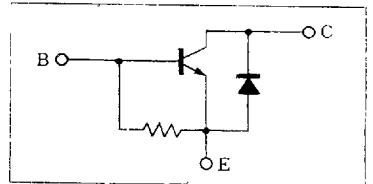
■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} =750 V, I _F =0			50	μA
		V _{CB} =1500 V, I _F =0			1	mA
Emitter-base voltage	V _{EB0}	I _E =500 mA, I _C =0	5			V
DC current gain	h _{FE}	V _{CE} =10 V, I _C =3 A	5		15	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =3 A, I _B =1 A			1	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =3 A, I _B =1 A			1.5	V
Transition frequency	f _T	V _{CE} =10V, I _C =0.5A, f=0.5MHz		2		MHz
Fall time	t _f	I _C =3A, I _{Bend} =1A			0.75	μs
Storage time	t _{stg}	L _{trak} =5μH	4		9	μs
Diode forward voltage	V _F	I _C =-4A, I _B =0			-2.2	V

■ Package Dimensions



■ Inner Circuit



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